

## 1. General description

Planar passivated thyristor module in industrial standard 34mm package for use in applications requiring high blocking voltage capability, high inrush current capability and high thermal cycling performance.

## 2. Features and benefits

- High blocking voltage capability
- High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability
- Product is RoHS compliant
- Industry standard outline
- Copper base plate
- Cathode Kelvin contacts provided

## 3. Applications

- Softstart AC motor control
- DC Motor control
- AC Motor control
- Power converter
- Temperature control
- Lighting control

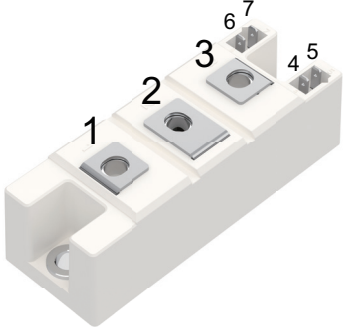
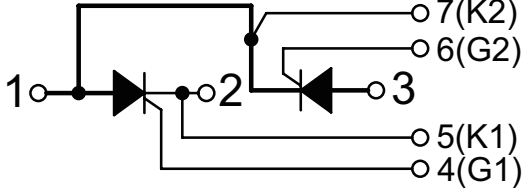
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
<b>Absolute maximum rating</b>							
$V_{DRM}$	repetitive peak forward voltage			1800			V
$V_{RRM}$	repetitive peak reverse voltage			1800			V
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_c = 87\text{ °C}$		314			A
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 10\text{ ms}$		5600			A
		half sine wave; $T_{j(init)} = 135\text{ °C}$ ; $t_p = 10\text{ ms}$		5100			A
		half sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 8.3\text{ ms}$		6160			A
		half sine wave; $T_{j(init)} = 135\text{ °C}$ ; $t_p = 8.3\text{ ms}$		5610			A
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
<b>Static characteristics</b>							
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.2\text{ A}$ ; $T_j = 25\text{ °C}$		-	-	150	mA
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.2\text{ A}$ ; $T_j = 25\text{ °C}$		-	-	2	V
$V_T$	on-state voltage	$I_T = 200\text{ A}$ ; $T_j = 25\text{ °C}$		-	-	1.3	V

## 5. Pinning information

Table 2. Pinning information

Simplified outline	Graphic symbol
	

## 6. Ordering information

Table 3. Ordering information

Type number	Orderable part number	Packing method	Small packing quantity
WTMH200S18	WTMH200S18T	Tray	16

## 7. Marking

Table 4. Marking codes

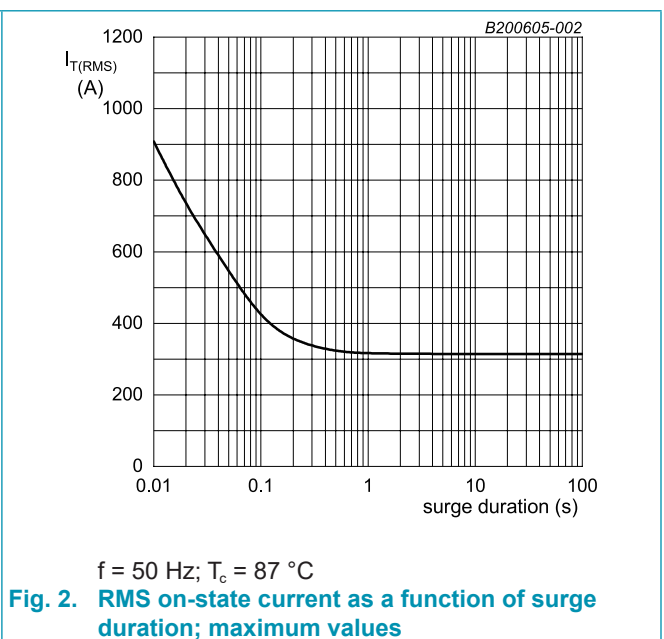
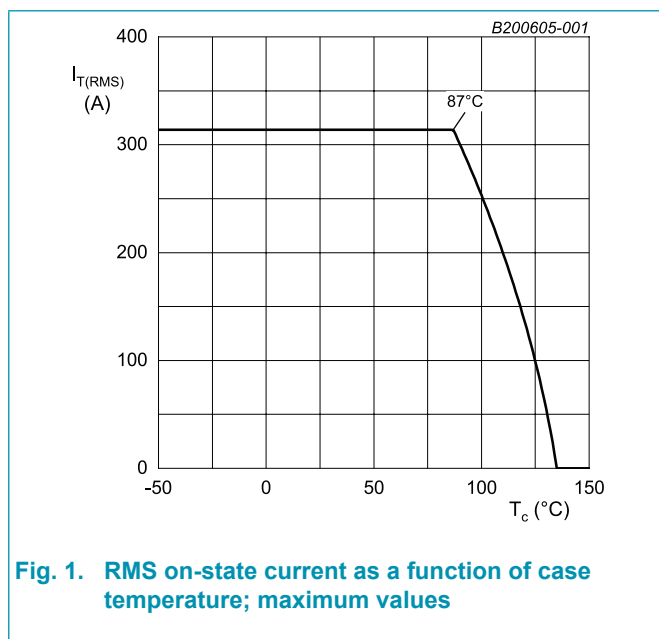
Type number	Marking codes
WTMH200S18	WTMH200S18

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{DSM}$	Non-repetitive peak forward voltage			1900	V
$V_{RSM}$	Non-repetitive peak reverse voltage			1900	V
$V_{DRM}$	repetitive peak forward voltage			1800	V
$V_{RRM}$	repetitive peak reverse voltage			1800	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_c = 87\text{ °C}$		200	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_c = 87\text{ °C}$		314	A
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 10\text{ ms}$		5600	A
		half sine wave; $T_{j(\text{init})} = 135\text{ °C}$ ; $t_p = 10\text{ ms}$		5100	A
		half sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 8.3\text{ ms}$		6160	A
		half sine wave; $T_{j(\text{init})} = 135\text{ °C}$ ; $t_p = 8.3\text{ ms}$		5610	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; sine-wave pulse		156.8	$\text{kA}^2\text{s}$
$di_T/dt$	rate of rise of on-state current	$I_G = 300\text{ mA}$		200	$\text{A}/\mu\text{s}$
$P_{GM}$	peak gate power			120	W
$P_{G(AV)}$	average gate power	over any 20 ms period		20	W
$T_{vj}$	virtual junction temperature			-40 to 135	$^{\circ}\text{C}$
$T_{op}$	operation temperature			-40 to 135	$^{\circ}\text{C}$
$T_{stg}$	storage temperature			-40 to 150	$^{\circ}\text{C}$



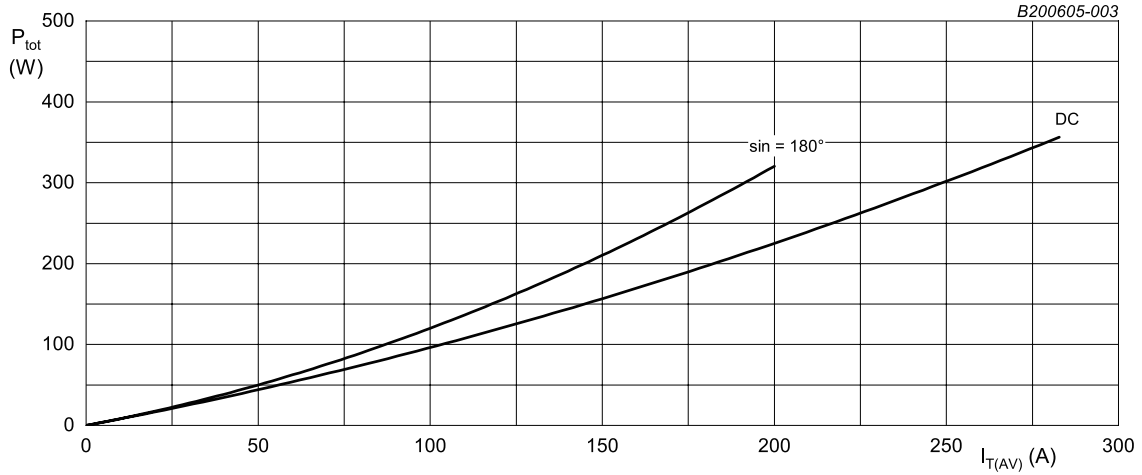
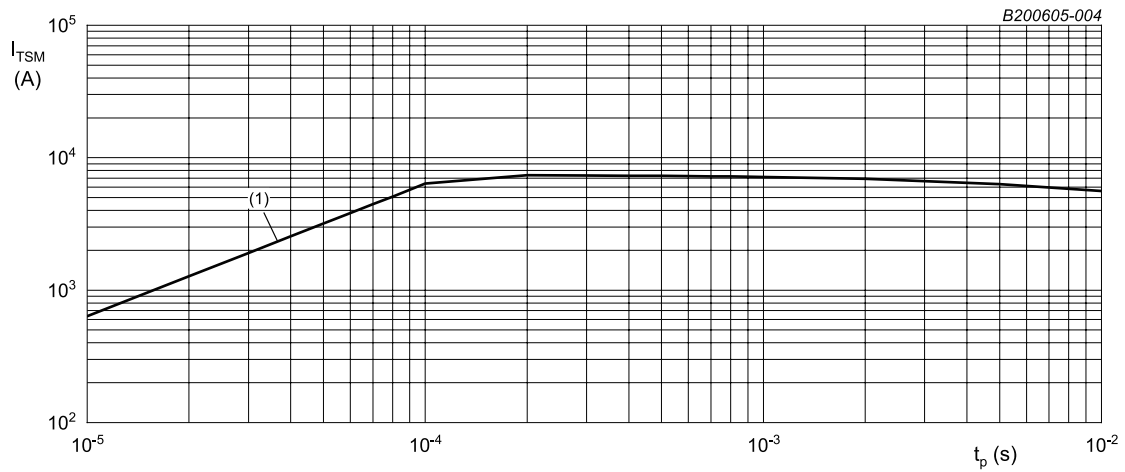


Fig. 3. Total power dissipation as a function of average on-state current; maximum values; per thyristor



$t_p \leq 10$  ms  
 (1)  $di_T/dt$  limit

Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	per thyristor	-	-	0.15	K/W
		per module	-	-	0.075	K/W
$R_{th(c-h)}$	thermal resistance from case to heatsink	per thyristor	-	-	0.1	K/W
		per module	-	-	0.05	K/W

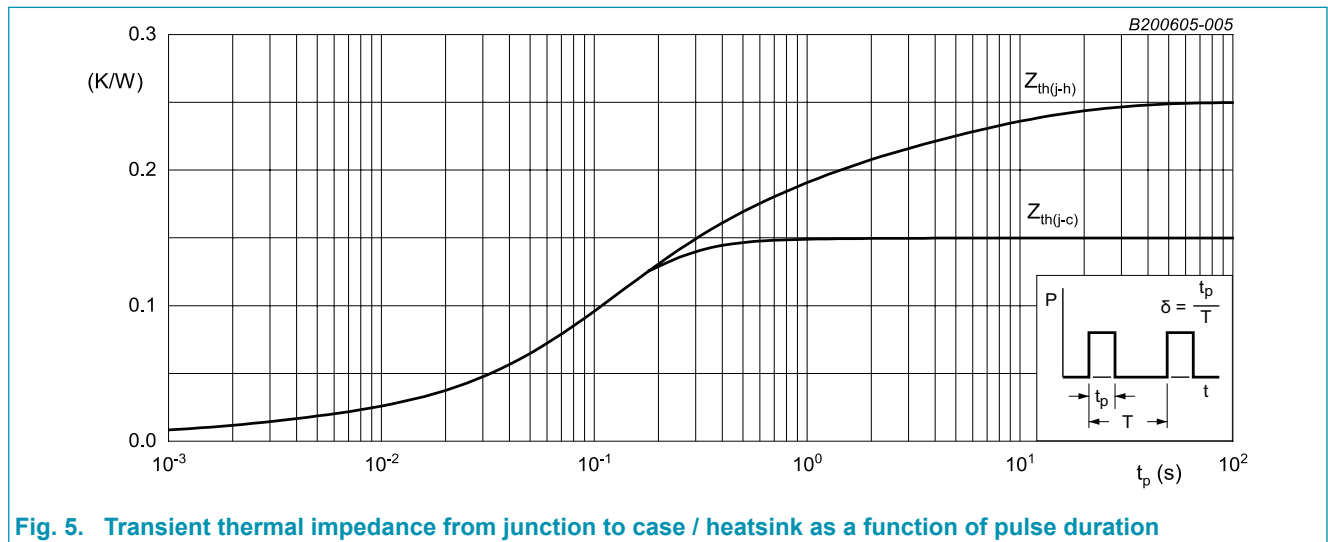


Fig. 5. Transient thermal impedance from junction to case / heatsink as a function of pulse duration

## 10. Package characteristics

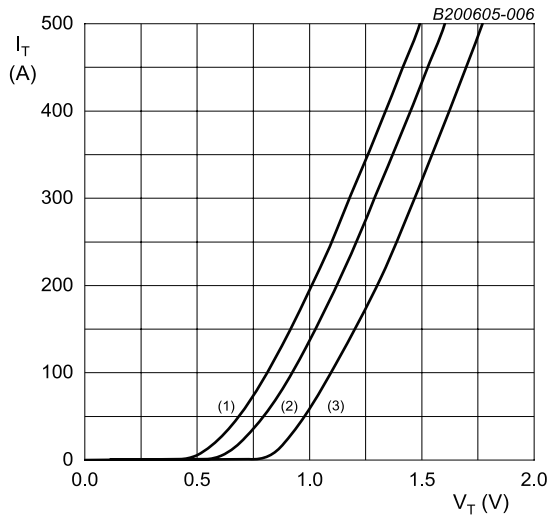
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol}$	isolation voltage	50/60 Hz; RMS; $I_{ISOL} \leq 1 \text{ mA}$ ; $t = 1 \text{ second}$ ; AC	-	-	3600	V
		50/60 Hz; RMS; $I_{ISOL} \leq 1 \text{ mA}$ ; $t = 1 \text{ minute}$ ; AC	-	-	3000	V

## 11. Characteristics

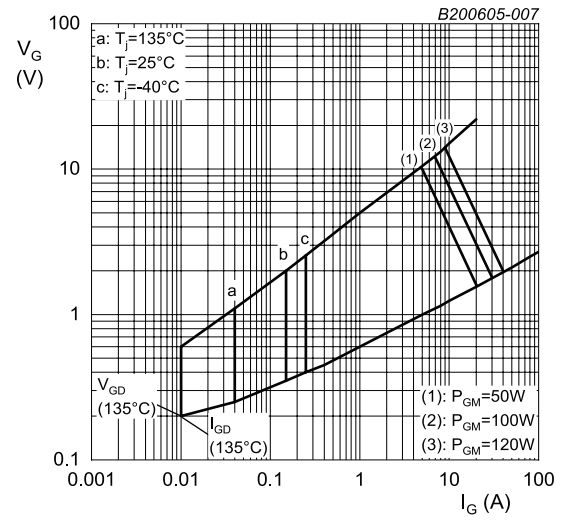
Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}; I_T = 0.2\text{ A}; T_j = 25\text{ °C}$	-	-	150	mA
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.2\text{ A}; T_j = 25\text{ °C}$	-	-	2	V
		$V_D = \frac{2}{3} V_{DRM}; I_T = 0.2\text{ A}; T_j = 135\text{ °C}$	0.25	0.48	-	V
$I_{GD}$	gate non-trigger current	$T_j = 135\text{ °C}$	-	-	10	mA
$V_{GD}$	gate non-trigger voltage	$T_j = 135\text{ °C}$	-	-	0.2	V
$I_L$	latching current	$V_D = 12\text{ V}; I_T = 0.2\text{ A}; T_j = 25\text{ °C}$	-	-	300	mA
$I_H$	holding current	$V_D = 12\text{ V}; T_j = 25\text{ °C}$	-	-	200	mA
$V_T$	on-state voltage	$I_T = 200\text{ A}; T_j = 25\text{ °C}$	-	-	1.3	V
$V_{TO}$	threshold voltage	$T_j = 135\text{ °C}$	-	-	0.8	V
$r_T$	slope resistance	$T_j = 135\text{ °C}$	-	-	1.6	mΩ
$I_D$	off-state current	$V_D = 1800\text{ V}; T_j = 25\text{ °C}$	-	-	100	μA
		$V_D = 1800\text{ V}; T_j = 135\text{ °C}$	-	-	10	mA
$I_R$	reverse current	$V_R = 1800\text{ V}; T_j = 25\text{ °C}$	-	-	100	μA
		$V_R = 1800\text{ V}; T_j = 135\text{ °C}$	-	-	10	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 1206\text{ V}; T_j = 135\text{ °C}; (V_{DM} = 67\% \text{ of } V_{DRM}); \text{exponential waveform; gate open circuit}$	1500	-	-	V/μs
$t_{gt}$	gate-controlled turn-on time	$V_D = 67\% \text{ of } V_{DRM}$	-	-	2	μs
$t_q$	commutated turn-off time	$V_R = 100\text{ V}; t_p = 50\text{ μs}; dV_D/dt = 5\text{ V/μs}; dI/dt = 30\text{ A/μs}; T_j = 135\text{ °C}$	-	150	-	μs



- (1)  $T_j = 135\text{ °C}$ ; typical values
- (2)  $T_j = 135\text{ °C}$ ; maximum values
- (3)  $T_j = 25\text{ °C}$ ; maximum values

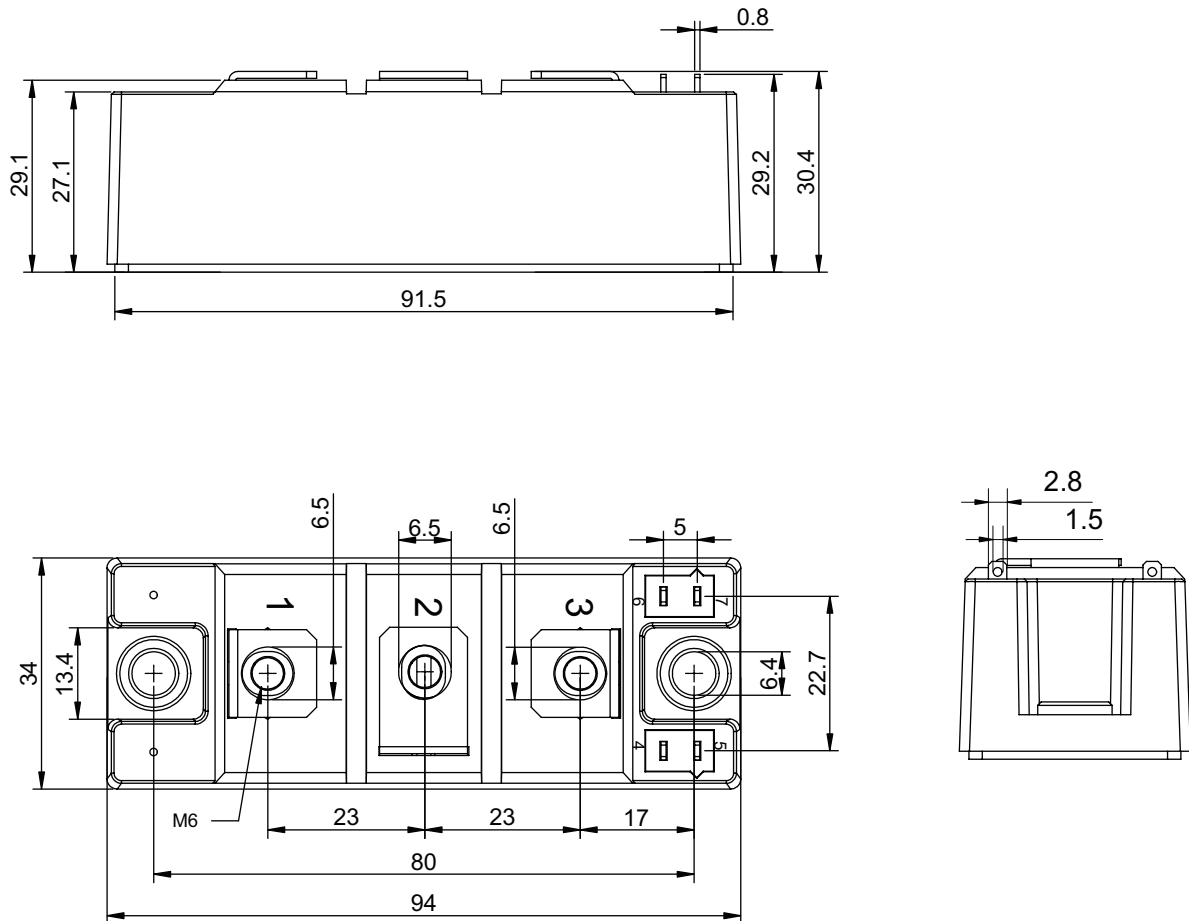
**Fig. 6. On-state current as a function of on-state voltage**



**Fig. 7. Gate voltage as a function of gate current**

## 12. Package outline

Dimensions in mm



General tolerance  $\pm 0.5\text{mm}$   
 Signal pins 4-7 are optional, defined by graphic symbol definition.

## 13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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